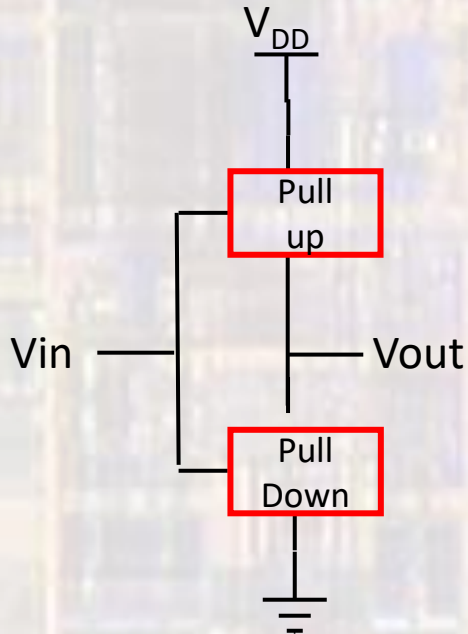


# C-MOS Circuits

Last updated 12/29/23

# C-MOS Circuits

- Gate Concepts



We can generalize our inverter results to account for more complex gates

Make the **effective**  $(W/L)_{pull-up} = 3 \times (W/L)_{pull-down}$

Mid supply switching point

Equivalent rise and fall times

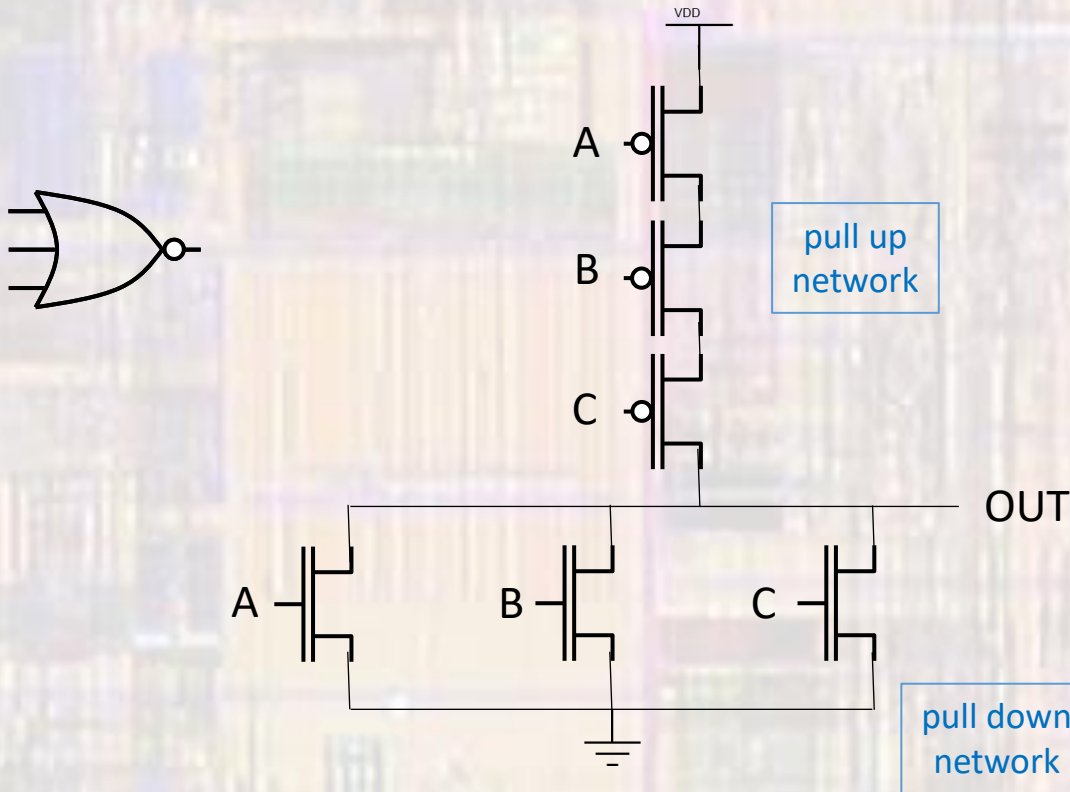
Remember the  $L$  of all devices is the same

$$W_{pull-up} = 3 \times W_{pull-down}$$

The ratio (3) is technology dependent

# C-MOS Circuits

- C-MOS Gates - NOR

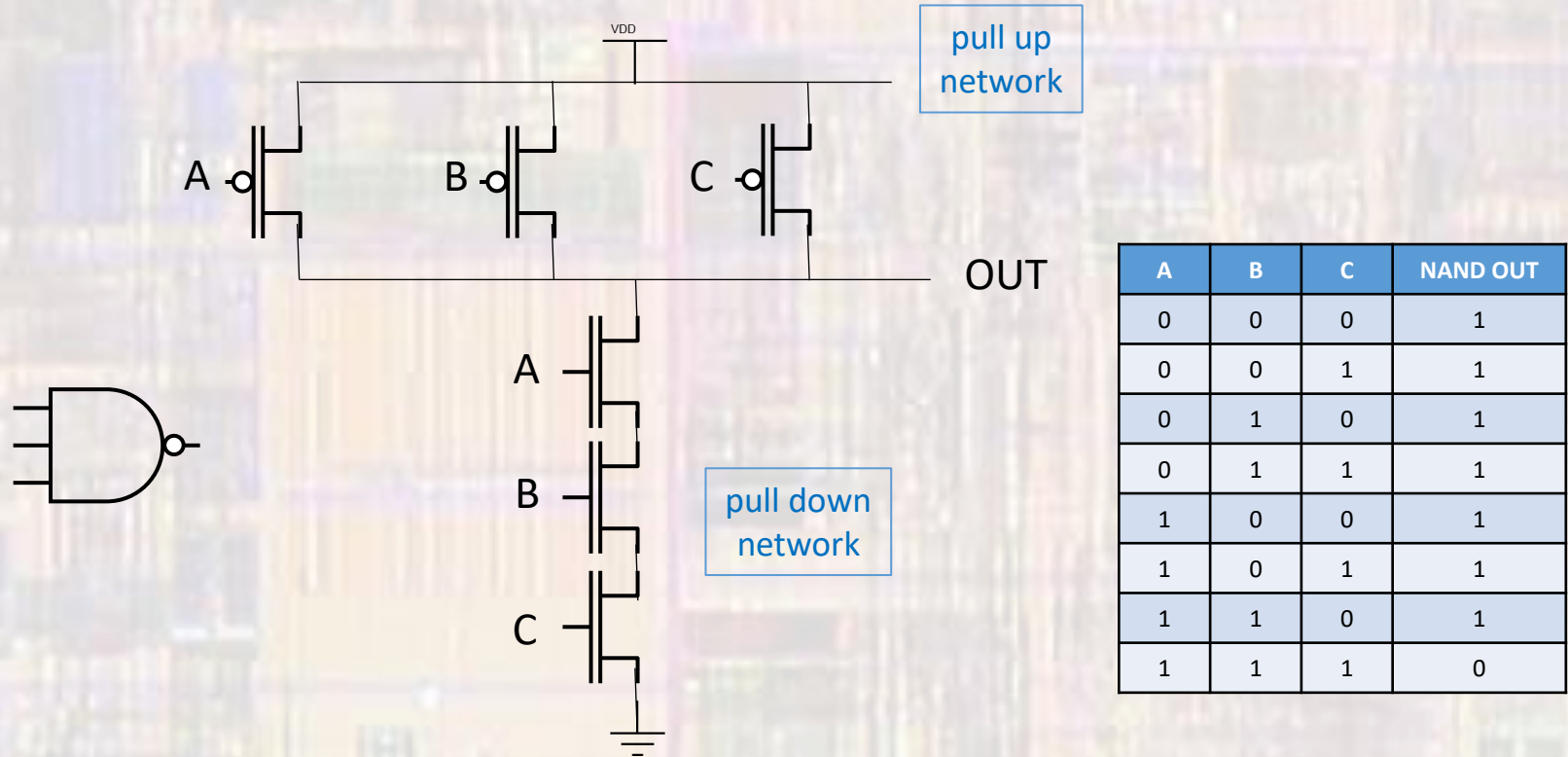


A	B	C	NOR OUT
0	0	0	1
0	0	1	0
0	1	0	0
0	1	1	0
1	0	0	0
1	0	1	0
1	1	0	0
1	1	1	0

If ANY input is high, pull-down is on, pull-up is off → output is low  
If ALL inputs are low, pull-down is off, pull-up is on → output is high

# C-MOS Circuits

- C-MOS Gates - NAND

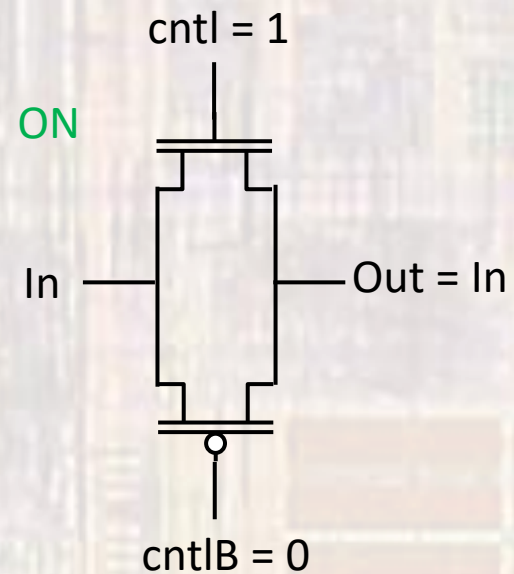
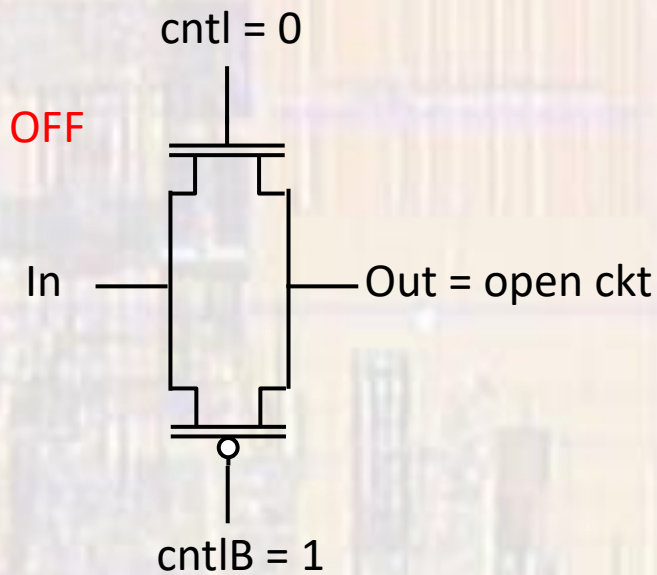


If ANY input is low, pull-up is on, pull-down is off → output is high  
If ALL inputs are high, pull-up is off, pull-down is on → output is low

# C-MOS Circuits

- C-MOS Transmission Gates

- Use parallel P-MOS and N-MOS devices as a “pass gate”
  - Passes both ‘0’s and ‘1’s
  - Bi-directional
  - Requires cntl and cntlB

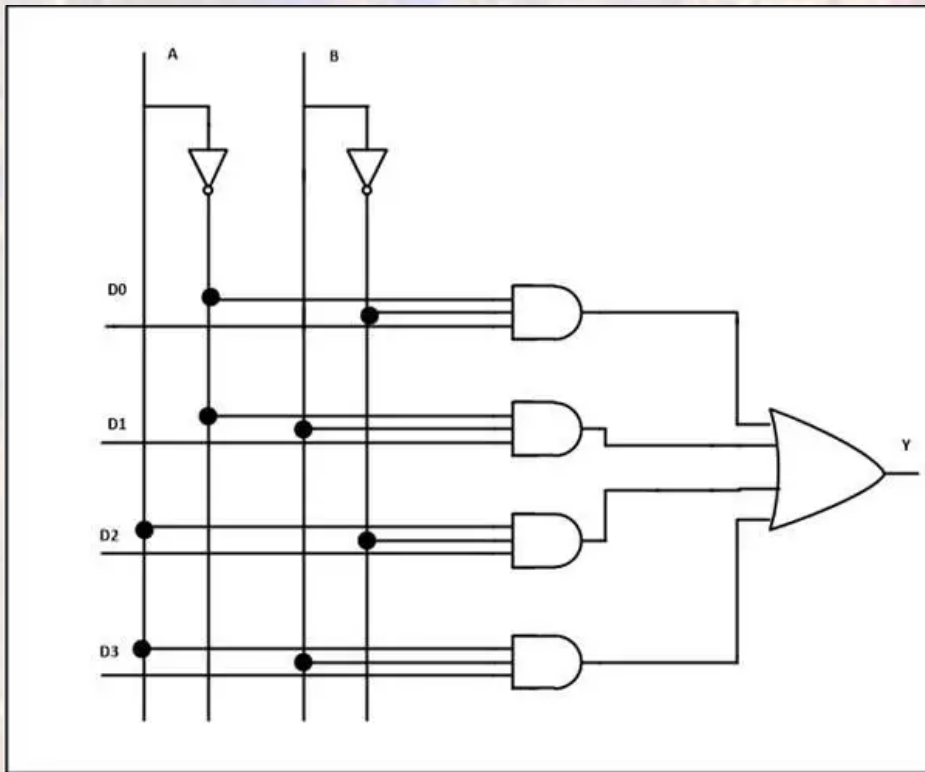




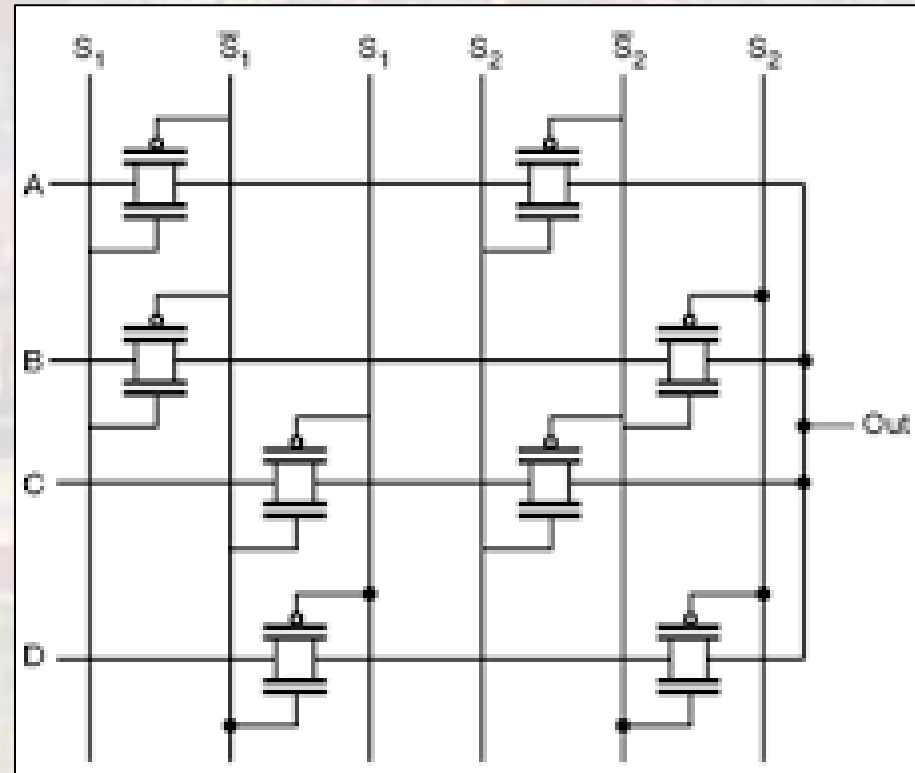
# C-MOS Circuits

- C-MOS Mux: 4::1

19 N-Channel, 19 P-Channel



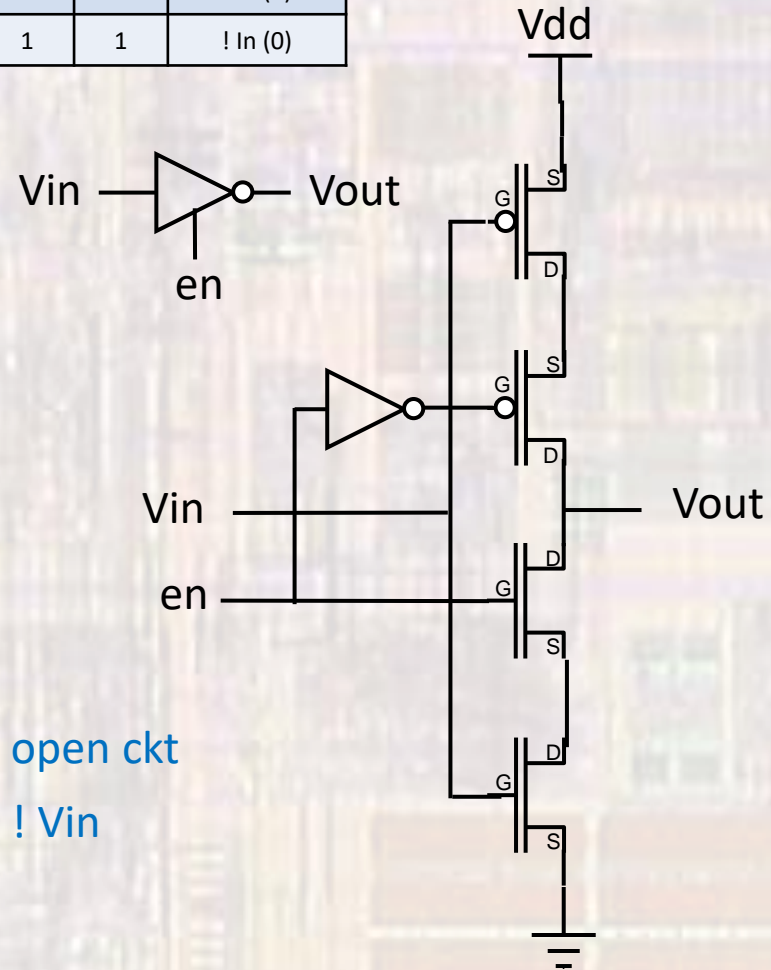
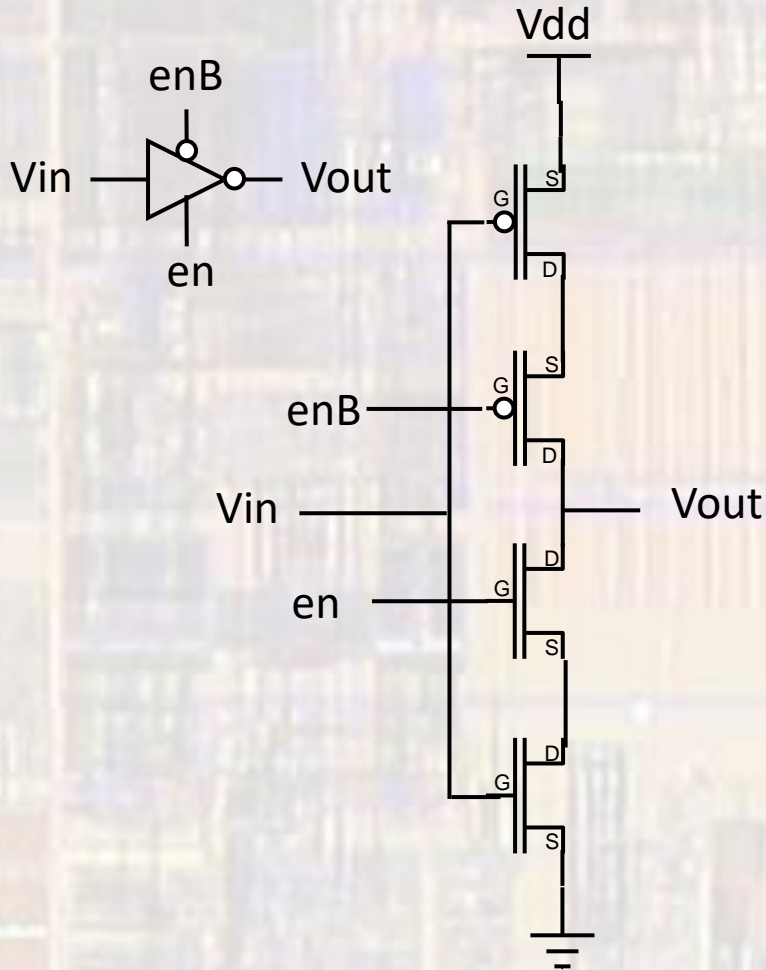
8 N-Channel, 8 P-Channel



# C-MOS Circuits

- C-MOS Tristate Inverter

en	in	OUT
0	0	Open ckt
0	1	Open ckt
1	0	! In (1)
1	1	! In (0)



$en = 0 \rightarrow Vout = \text{open ckt}$   
 $en = 1 \rightarrow Vout = ! Vin$